

Abstract of the Disclosure

The present invention provides a semiconductor memory device capable of being stably operated by reducing power noise generated while a sense amplifier performing for sensing and amplifying data supplied to a bit line. For this object, an inventive semiconductor memory device includes a cell array having a plurality of cells; a plurality of bit lines supplied with voltage stored in the plurality of the cells; a plurality of sense amplifier block for sensing and amplifying a voltage of the plurality of the bit lines, each bit line being connected to each cell; a plurality of switches for selectively connecting or disconnecting the plurality of the sense amplifier block to the plurality of the bit lines; and a sense amplifier control block for turning on the plurality of the switches by using at least two different timing sets.